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TI-35330  
RHK

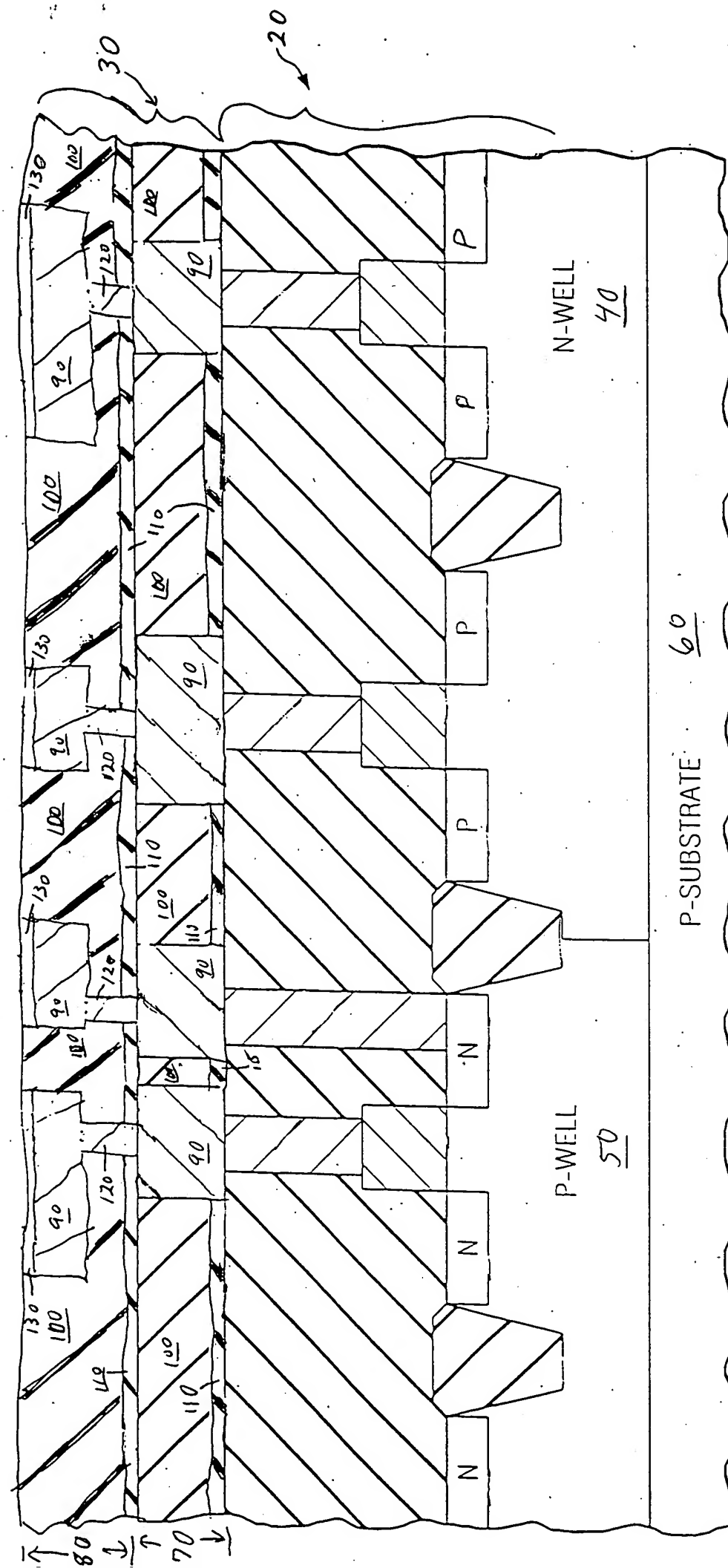


FIG. 1

200 - Formation of barrier layer  
(optional)

210 - Formation of dielectric layer

220 - Pattern + etch of <sup>the</sup> dielectric layer and ~~strip~~ the barrier layer (if used)

230 - Barrier metal and Copper deposition

240 - Copper CMP

260 - Post-CMP clean

280 - Formation of next dielectric layer

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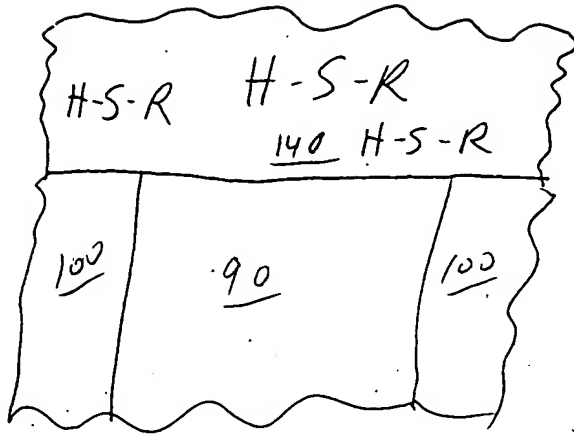


FIG. 3A

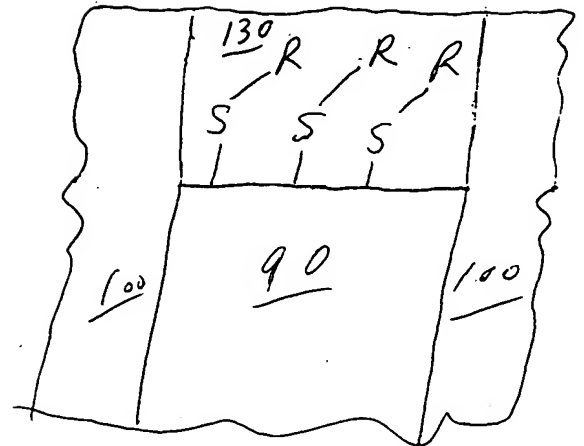


FIG. 3B

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